

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): ~~High purity hafnium and a target and thin film formed from said high purity hafnium~~ having a purity of 4N or higher excluding zirconium and gas components, and an oxygen content of 40wtppm or less, a sulfur content of 10wtppm or less, a phosphorus content of 10wtppm or less, and a zirconium content of 0.1wt% or less.

Claim 2 (currently amended): ~~High purity hafnium and a~~ A sputtering target and or thin film, comprising a sputtering target or thin film formed from said of high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, an oxygen content of 40wtppm or less, and in which the content of a sulfur and content of 10wtppm or less, a phosphorus is respectively content of 10wtppm or less, and a zirconium content of 0.1wt% or less.

Claims 3-4 (canceled).

Claim 5 (currently amended): A method of manufacturing method of high purity hafnium, comprising the steps of:

~~wherein~~ subjecting a hafnium ~~sponge~~ raw material ~~is subject~~ to solvent extraction and thereafter ~~dissolved~~ dissolving the raw material,

~~and the obtained obtaining a hafnium ingot is further subject from the raw material after~~
~~said solvent extraction and subjecting the ingot~~ to deoxidation with molten salt,
~~and~~
~~after said deoxidation, subjecting the ingot to electron beam melting.~~

Claim 6 (canceled).